

COMPLEMENTARY SILICON PLASTIC POWER TRANSISTORS

... designed for use as output device in complementary audio amplifiers up to 30-Watts music power per channel

FEATURES:

*Collector-Emitter Sustaining Voltage-

V_{CEO(SUS)} = 60 V (Min) * DC Current Gain-

hFE = 25-100 @ Ic = 3.0 A

NPN PNP MJE2801T MJE2901T

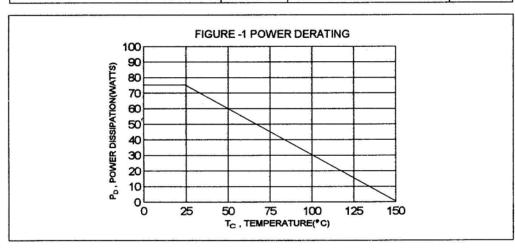
10 AMPERE COMPLEMENTARY SILICON **POWER TRANASISTORS** 60 VOLTS 75 WATTS

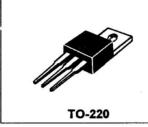
MAXIMUM RATINGS

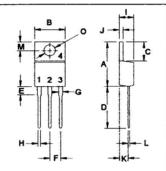
Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	60	V
Collector-Base Voltage	V _{CBO}	60	V
Emitter-Base Voltage	V _{EBO} 4.0		V
Collector Current - Continuous - Peak	I _C	10 15	A
Base current	l _B	5.0	A
Total Power Dissipation @T _C = 25°C Derate above 25°C	P _D	75 0.6	W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	1.67	°C/W







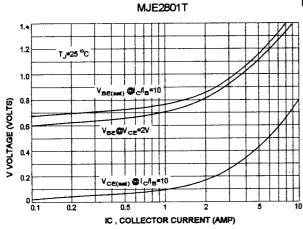
PIN 1.BASE 2.COLLECTOR
3.EMITTER
4.COLLECTOR(CASE)

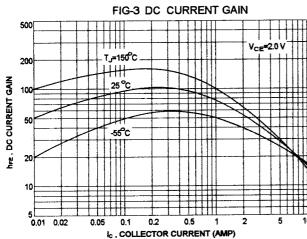
DIM	MILLIMETERS		
DIN	MIN	MAX	
Α	14.68	16.00	
В	9.78	10.42	
С	5.02	6.60	
D	13.00	14.62	
E	3.10	4.19	
F	2.41	2.67	
G	1.10	1.67	
Н	0.69	1.01	
I	3.21	4.98	
J	1.14	1.40	
K	2.20	3.30	
L	0.28	0.61	
М	2.48	3.00	
0	3.50	4.00	

ELECTRICAL CHARACTERISTICS (T_c = 25°C unless otherwise noted)

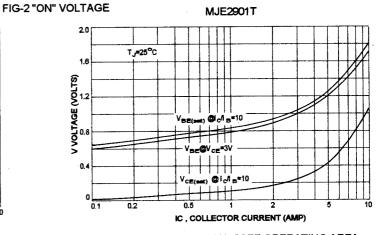
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (1) (I _C = 200 mA, I _B = 0)	V _{CEO}	60	-	V
Collector Cutoff Current $(V_{CB} = 60 \text{ V}, I_E = 0)$ $(V_{CB} = 60 \text{ V}, I_E = 0, T_C = 150 ^{\circ}\text{C})$	СВО		0.1 2.0	mA
Emitter Cutoff Current (V _{EB} = 4.0 V , I _C = 0)	I _{EBO}		1.0	mA
ON CHARACTERISTICS (1)				
DC Current Gain (I _C = 3.0 A, V _{CE} = 2.0 V)	hFE	25	100	
Base-Emitter On Voltage (I _C = 3.0 A, V _{CE} = 2.0 V)	V _{BE(on)}		1.4	V

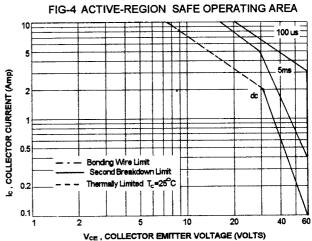
(1) Pulse Test: Pulse Width =300 us, Duty Cycle ≤ 2.0%





There are two limitation on the power handling ability of a transistor :average junction temperature and second breakdown safe operating area curves indicate Ic-VcE limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.





The data of FIG-4 is base on $T_{\text{J/PK)}}$ =150 °C; T_{C} is variable depending on conditions.second breakdown pulse limits are valid for duty cycles to 10% provided $T_{\text{J/PK)}}$ <150°C ,At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



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